

Type	Operational Data					Maximum Ratings	
KF506 KF507 KF508 Silicon n-p-n planar transis- tors for R. F. amplifiers		KF506	KF507	KF508	measured at	KF506 KF508	
	I_{CBO}	<10	—	<10	nA	$U_{CB} = 60$ V	U_{CB} 75 V
	I_{CBO}	—	<500	—	nA	$U_{CB} = 30$ V	U_{EB} 7 V
	U_{CES}	<1,5	<1,5	<1,5	V	$I_C = 150$ mA, $I_B = 15$ mA	$U_{CER} (R_{BE} < 500 \Omega)$
	U_{BES}	0,95	<1,3	—	V	$I_C = 150$ mA, $I_B = 15$ mA	KF506 50 V
	I_B	<1	—	—	μ A	$U_{CB} = 10$ V, $-I_E = 5 \mu$ A	KF508 60 V
	I_B	80–290	<290	33–110	μ A	$U_{CB} = 10$ V, $-I_E = 10$ mA	
	I_B	<3,75	<3,75	<1,5	mA	$U_{CB} = 10$ V, $-I_E = 150$ mA	
	h_{21E}	35–125	>35	90–300	—	$U_{CB} = 10$ V, $-I_E = 10$ mA	KF507
	h_{21E}	85>40	100>40	150>100	—	$U_{CB} = 10$ V, $-I_E = 150$ mA	U_{CB} 40 V
	h_{21E}	55>20	>20	75>40	—	$U_{CB} = 10$ V, $-I_E = 500$ mA	$U_{CER} (R_{BE} < 500 \Omega)$
	$r_{b\beta'}$	35	35	35	Ω	$U_{CB} = 10$ V, $-I_E = 0,3$ mA, $f = 1$ kHz, $\Delta f \approx 200$ Hz	32 V
	F	4<10	6	3,5<8	dB	$U_{CB} = 10$ V, $-I_E = 10$ mA, $f = 2$ MHz	U_{EB} 5 V
	C_{22b}	—	18<25	—	pF	$U_{CB} = 10$ V, $-I_E = 0$ mA, $f = 2$ MHz	I_C 500 mA
	f_T	100>60	100>50	120>70	MHz	$U_{CB} = 10$ V, $-I_E = 50$ mA, $f = 30$ MHz	$-I_E$ 500 mA
	U_{CBO}	>75	>40	>75	V	$I_C = 0,1$ mA	I_B 50 mA
	U_{EBO}	>7	>5	>7	V	$I_E = 0,1$ mA	P_{tot} 0,8 W
	Outlines K 505						$P_{tot}^1)$ 2,6 W
							T_j 200 °C
						R_{t1} 60 °C/W	
						R_t 220 °C/W	
						T_a -65...+200 °C	
						2) With ideal cooling	

Silicon n-p-n
planar transis-
tors for R. F.
amplifiers

